Pentacoordinate Silicon(IV): Cationic, Anionic and Neutral Complexes Derived from the Reaction of NHC→SiCl₄ with Highly Lewis Acidic (C₂F₅)₂SiH₂.

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1. Experimental Section

General remarks

All reactions were carried out under an atmosphere of dry nitrogen using standard Schlenk-line techniques unless mentioned otherwise. Solvents were dried using a Braun MB-SPS 800 system. Acetonitrile and dichloromethane were stored under 3 Å molecular sieves. Deuterated acetonitrile (CD₃CN) was distilled over CaH₂. All other chemicals were purchased from available commercial sources and were used as received. NMR spectra were recorded on a Bruker Model Avance III 300 spectrometer (Operating frequencies: ²⁹Si 59.63 MHz, ¹⁹F 282.40 MHz, ¹³C 75.47 MHz, ¹H 300.13 MHz) with positive shifts being downfield from the external standards (CCl₃F (¹⁹F), Si(CH₃)₄ (²⁹Si, ¹³C, ¹H)). The ¹³C and ²⁹Si NMR shifts were aquired by ¹H,¹³C and ¹H,²⁹Si 2D HMBC NMR correlation experiments. Elemental analyses were performed by the microanalytical laboratory of the department of Inorganic Chemistry II (ACII), University of Bielefeld, Bielefeld, Germany. Compounds NHC-SiCl₄ (1), Cl₂Si(C₂F₅)₂ (2) and H₂Si(C₂F₅)₂ (3) were prepared according to procedures reported elsewhere.^[1,2]

Synthesis of $[(NHC)_2SiCl_2H][(C_2F_5)_2SiCl_3]$ (4)

A solution of **1** (2.34 g, 8.73 mmol) in acetonitrile (60 ml) was placed in a 100 ml Schlenk flask. The solution was cooled to -196 °C and **3** (5.0 mmol, 1.1 eq.) was condensed into the flask. The reaction mixture was allowed to reach room temperature over a period of 12 h under constant stirring. All volatile components were removed under reduced pressure. The residue was washed three times with 20 ml of diethyl ether. Drying in vacuo gave **4** (2.85 g, 4.26 mmol, 98% raw yield, based on **1**). Single crystals of **4** were obtained from a solution of **4** in acetonitrile stored at -28 °C (1.20 g, 1.79 mmol, 41% based on **1**).

Yield: 41% (based on 1). Elemental analysis calcd (%) for $C_{14}H_{21}N_4F_{10}Si_2Cl_5$ (668.76): C 25.14, H 3.17, N 8.38; found: C 24.94, H 3.70, N 8.49.¹H NMR (CD₃CN) δ = 3.30 (s, 12H, -CH₃), 3.85 (s, 8H, -CH₂-), 6.71 (s, 1H, Si-H, ¹*J*_{SiH} = 352 Hz). ¹H,¹³C HMBC NMR (CD₃CN) δ (¹H)/ δ (¹³C): 3.30/36.5 (d, -CH₃/-CH₃, ¹*J*_{CH} = 141 Hz), 3.30/51.7 (s, -CH₃/-CH₂-), 3.85/51.7 (d,m, -CH₂-/-CH₂-, ¹*J*_{CH} = 153 Hz), 3.30/171.2 (s, -CH₃/C_{carbene}), 3.85/171.2 (s, -CH₂-/C_{carbene}). ¹⁹F NMR (CD₃CN): δ = -118.6 (s, 4F, -CF₂-), -75.8 (s, 6F, -CF₃). ¹H,²⁹Si HMBC NMR (CD₃CN) $\delta({}^{1}\text{H})/\delta({}^{29}\text{Si}) = 3.30/-125.4 \text{ (s, -CH}_{3}/\text{Si}), 3.85/-125.4 \text{ (s, -CH}_{2}-/\text{Si}), 6.71/-125.4 \text{ (d, Si-H/Si, }{}^{1}J_{\text{SiH}} = 352 \text{ Hz}).$ ¹⁹F,²⁹Si HMBC NMR (CD₃CN) $\delta({}^{19}\text{F})/\delta({}^{29}\text{Si}) = -118.6/-96.6 \text{ (d, -CF}_{2}-/\text{Si}, \, {}^{2}J_{\text{SiF}} = 44 \text{ Hz}).$

Synthesis of NHC-SiCl₃H (5)

A solution of **1** (2.81 g, 10.48 mmol) in dichloromethane (50 ml) was placed in a 100 ml Schlenk flask. Silicochloroform (1.42 g 10.48 mmol, 1 eq.) was condensed into the solution at -196 °C. The reaction mixture was allowed to reach room temperature and was stirred for another 2.5 h. Removal of all volatile components gave a colorless solid (2.36 g). The raw product was then dissolved in acetonitrile (20 ml) and diethyl ether was slowly condensed into the solution at -30 °C. After 7 days single crystals suitable for XRD of **5** were obtained. In solution, a dismutation process to compounds **1** and **6** takes place. Compound **5** co-crystallizes with compound **1**. Yield: 1.22 g (with 10% of compound **1** according to ¹H NMR and as observed in XRD).

Yield: 50% (based on 1). ¹H NMR (CD₃CN) δ = 3.30 (s, 6H, -CH₃), 3.77 (s, 4H, -CH₂-), 6.80 (s, 1H, Si-H, ¹*J*_{SiH} = 393 Hz). ¹³C, ¹H HMBC (CD₃CN) δ (¹³C)/ δ (¹H) = 3.30/34.5 (d, -CH₃/-CH₃, ¹*J*_{CH} = 140 Hz), 3.30/51.1 (, -CH₃/-CH₂-), 3.77/51.1 (d,m, -CH₂-/-CH₂-, ¹*J*_{CH} = 152 Hz), 3.30/173.1 (s, -CH₃/-CH₂-), 6.80/173.1 (d, Si-H/C_{carbene}, ²*J*_{CH} = 8 Hz). ²⁹Si, ¹H HMBC NMR (CD₃CN) δ (²⁹Si)/ δ (¹H) = 3.30/-104.5 (s, -CH₃/Si), 6.80/-104.5 (d, -Si-H/Si, ¹*J*_{SiH} = 393 Hz). ²⁹Si, ¹H DEPT NMR (CD₃CN) δ = -104.5 (d, ¹*J*_{SiH} = 393 Hz).

Synthesis of NHC-SiCl₂H₂ (6)

A solution of 1 (1.50 g, 5.60 mmol) in tetrahydrofuran (30 ml) was placed in a 100 ml Schlenk flask. Silicochloroform (23 mmol, 4 eq.) was condensed into the solution at -196 °C. The reaction mixture was allowed to reach room temperateure and was stirred for additional 12 h. After removal of all volatile components, the crude product was dissolved in a minimum amount of acetonitrile and diethyl ether was slowly condensed into the solution. Removal of all volatile components gave compound **6** (1.09 g, 5.47 mmol). Single crystals were obtained by slow diffusion of diethyl ether into a saturated solution of **6** in acetonitrile.

Yield: 98% (based on 1). ¹H NMR (CD₃CN) $\delta = 3.25$ (s, 6H, -CH₃), 3.77 (s, 4H, -CH₂-), 6.11 (s, 2H, Si-H, ¹*J*_{SiH} = 333 Hz). ¹H, ¹³C HMBC (CD₃CN) δ (¹H)/ δ (¹³C) = 3.25/34.5 (d, -CH₃/-CH₃, ¹*J*_{CH} = 140 Hz), 3.25/51.1 (s, -CH₃/-CH₂-), 3.77/51.1 (d,m, -CH₂-/-CH₂-, ¹*J*_{CH} = 153 Hz), 3.25/175.4 (s, -CH₃/C_{carbene}), 3.77/175.4 (s, -CH₂-/C_{carbene}), 6.11/175.4 (s, Si-H/C_{carbene}). ²⁹Si NMR (CD₃CN) δ = -125.2 (t, ¹*J*_{SiH} = 333 Hz). ¹H, ²⁹Si HMBC NMR (CD₃CN) δ (¹H)/ δ (²⁹Si) = 3.25/-125.2 (s, -CH₃/Si), 3.77/-125.2 (s, -CH₂-/Si), 6.11/-125.2 (d, Si-H/Si, ¹*J*_{SiH} = 333 Hz). ²⁹Si, ¹H DEPT NMR (CD₃CN) δ = -125.2 (t, ¹*J*_{SiH} = 333 Hz).

2. Crystallographic section

X-ray crystallography

Single crystals were coated with a layer of hydrocarbon oil and attached to a MicroMountTM. Crystallographic data were collected with a SuperNova, Dual, Cu at zero, Atlas diffractometer with Mo-K α or Cu-K α radiation (multilayer mirror monochromator, $\lambda = 0.71073$ Å resp. 1.5418 Å) at 100 K. Crystallographic programs used for structure solution and refinement were from SHELX -97.^[3] The structures were solved by direct methods and were refined by using full-matrix least squares on F² of all unique reflections with anisotropic thermal parameters for all non-hydrogen atoms, except disordered atoms of the lower occupancy in compound **4**. All hydrogen atoms bonded to silicon were refined isotropically. All hydrogen atoms bonded to carbons were refined isotropically using a riding model with U(H) = 1.5 U_{eq} for CH₃ groups and U(H) = 1.2 U_{eq} for all others, excluding the hydrogen atoms of compound **4** which were all refined isotropically.

CCDC contains supplementary crystallographic data for this paper. These data can be obtained free of charge from The Cambridge Crystallographic Data Centre via www.ccdc.cam.ac.uk/data_request/cif.

The crystal data, refinement parameters and CCDC depositons numbers for all complexes are given in Table S1.

Parameter	4	5	6
Empirical formula	$C_{14}H_{21}Cl_5F_{10}N_4Si_2\\$	0.9 x C ₅ H ₁₁ Cl ₃ N ₂ Si	C ₅ H ₁₂ N ₂ SiCl
Empirical formula		$0.1 \ge C_5 H_{10} C l_4 N_2 S i$	2
Formula weight	668.78	236.88	199.16
Temperature [K]	100.0(1)	100.0(1)	100.0(1)
Radiation used	Cu-Ka	Μο-Κα	Μο-Κα
Crystal system	triclinic	orthorhombic	monoclinic
Space group	P-1	Pbca	$P2_{I}/c$
a [Å]	8.1924(2)	13.05642(14)	9.9722(3)
b [Å]	12.5273(3)	10.62115(11)	12.2770(3)
c[Å]	13.0812(3)	14.80917(14)	7.76332(14)
α [°]	89.833(2)	90	90
β[°]	81.713(2)	90	90.020(2)
γ [°]	79.902(2)	90	90
Volume [Å ³]	1307.57(6)	2053.65(4)	950.45(4)
Z	2	8	4
$\rho_{calc} [mg/mm^3]$	1.699	1.532	1.392
μ [mm ⁻¹]	6.743	0.979	0.745
F(000)	672.0	972.0	416.0
	0.28 × 0.10 × 0.00	0.26 × 0.24 × 0.18	0.16×0.14
Crystal size [mm ³]	$0.38 \times 0.10 \times 0.09$ $0.26 \times 0.24 \times 0.000$	$0.26 \times 0.24 \times 0.18$	× 0.11
2Θ range for data collection	6 to 144°	6 to 60°	6 to 60°
Reflections collected	22010	136389	56379
Independent reflections	5116	3005	2767
R(int)	0.0246	0.0375	0.0732
Data/restraints/parameters	5116/0/430	3005/0/125	2767/1/100
Goodness-of-fit on F ²	1.101	1.184	1.057
$R_1[I > 2 \sigma(I)]^a$	0.0240	0.0289	0.0507
R_w (all data) ^b	0.0625	0.0766	0.1323
Largest diff. peak/hole / eÅ ⁻³	0.54/-0.34	0.44/-0.48	1.16/-0.78
CCDC deposition no.	965803	965804	965805

 Table S1. Crystallographic parameters for compounds 4, 5, and 6.

 ${}^{\mathrm{a}}R_{I} = \Sigma ||F_{\mathrm{o}}| - |F_{\mathrm{c}}|| / \Sigma |F_{\mathrm{o}}|. {}^{\mathrm{b}}R_{w} = \{\Sigma [w(F_{\mathrm{o}}^{2} - F_{\mathrm{c}}^{2})^{2}] / \Sigma [w(F_{\mathrm{o}}^{2})^{2}] \}^{1/2}$

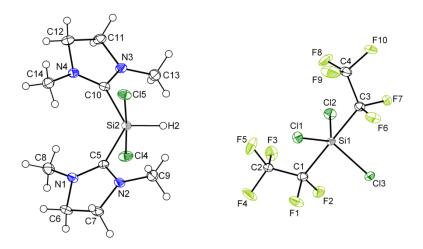


Figure S1. Atom labeling for the crystal structure of **4** (cation and anion are depicted indepentently).

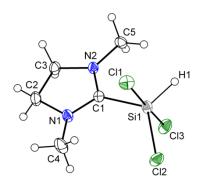


Figure S2. Atom labeling for the crystal structure of 5.

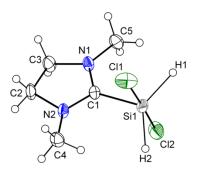


Figure S3. Atom labeling for the crystal structure of 6.

3. References

- a) B. Hoge, S. Steinhauer, J. Bader, N. Ignati'ev, 20th Symposium on Fluorine Chemistry, Kyoto, Japan 2012; b) B. Hoge, S. Steinhauer, N. Ignati'ev, 6th European Silicon Days, Lyon, France 2012; c) B. Hoge, S. Steinhauer, Manuscript in preparation.
- T. Böttcher, B. S. Bassil, L. Zhechkov, T. Heine, G.-V. Röschenthaler, *Chem. Sci.* 2013, 4, 77.
- [3] Sheldrick, G. M., Acta Crystallogr., Sect. A: Found. Crystallogr. 2008, 64, 112.